

STPS5H100

High voltage power Schottky rectifier

Main product characteristics

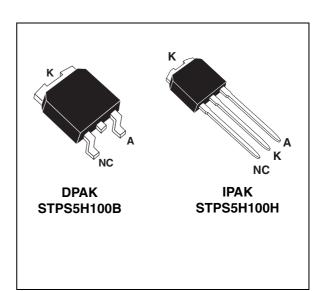
I _{F(AV)}	5 A
V _{RRM}	100 V
T _j (max)	175° C
V _F (max)	0.61 V

Features and benefits

- Negligible switching losses
- High junction temperature capability
- Low leakage current
- Good trade off between leakage current and forward voltage drop
- Avalanche specification

Description

This high voltage Schottky barrier rectifier is packaged in DPAK and IPAK, and designed for high frequency miniature switched mode power supplies such as adaptators and on board DC to DC converters.



Order codes

Part number	Marking
STPS5H100B	S5H100
STPS5H100B-TR	S5H100
STPS5H100H	S5H100H

Parame	Value	Unit	
Repetitive peak reverse voltage	100	V	
RMS forward voltage	RMS forward voltage		
Average forward current	Average forward current $T_c = 165^\circ C \delta = 0.5$		
Surge non repetitive forward current	e non repetitive forward current t _p =10 ms sinusoidal		Α
Repetitive peak reverse current $t_p = 2 \ \mu s \ F = 1 \ KHz$		1	Α
Non repetitive peak reverse current $t_p = 100 \ \mu s \ square$		2	Α
Repetitive peak avalanche power	7200	W	
Storage temperature range	-65 to + 175	°C	
Maximum operating junction temperature ⁽¹	175	°C	
Critical rate of rise of reverse voltage			V/µs
	Repetitive peak reverse voltage RMS forward voltage Average forward current Surge non repetitive forward current Repetitive peak reverse current Non repetitive peak reverse current Repetitive peak avalanche power Storage temperature range Maximum operating junction temperature ⁽¹⁾	RMS forward voltageAverage forward current $T_c = 165^{\circ} C \ \delta = 0.5$ Surge non repetitive forward current $t_p = 10 \ ms \ sinusoidal$ Repetitive peak reverse current $t_p = 2 \ \mu s \ F = 1 \ KHz$ Non repetitive peak reverse current $t_p = 100 \ \mu s \ square$ Repetitive peak avalanche power $t_p = 1 \ \mu s \ T_j = 25^{\circ} \ C$ Storage temperature rangeMaximum operating junction temperature ⁽¹⁾	$\begin{array}{ccc} \mbox{Repetitive peak reverse voltage} & 100 \\ \mbox{RMS forward voltage} & 10 \\ \mbox{Average forward current} & T_c = 165^\circ C \ \delta = 0.5 & 5 \\ \mbox{Surge non repetitive forward current} & t_p = 10 \ \mbox{ms sinusoidal} & 75 \\ \mbox{Repetitive peak reverse current} & t_p = 2 \ \mbox{µs F} = 1 \ \mbox{KHz} & 1 \\ \mbox{Non repetitive peak reverse current} & t_p = 100 \ \mbox{µs square} & 2 \\ \mbox{Repetitive peak avalanche power} & t_p = 1 \ \mbox{µs T}_j = 25^\circ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$

1. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Characteristics 1

Table 2. Thermal resistance	Table 2.	Thermal resistance
-----------------------------	----------	--------------------

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case	2.5	°C/W

Table 3. Static electrical characteristics

Symbol	Parameter	Test con	Min.	Тур.	Max.	Unit	
IR ⁽¹⁾ Reverse leakage current	Povereo lookogo ourrent	T _j = 25° C	V – V			3.5	μA
	T _j = 125° C	V _R = V _{RRM}		1.3	4.5	mA	
		$T_j = 25^\circ C$	I _F = 5 A			0.73	
V _F ⁽²⁾ Forward voltage drop	T _j = 125° C	IF = 0 X		0.57	0.61	v	
	T _j = 25° C	I _F = 10 A			0.85	v	
		$T_j = 125^\circ C$	ч _F – 10 А		0.66	0.71	

1. Pulse test: tp = 5 ms, δ < 2%

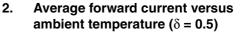
2. Pulse test: tp = 380 μ s, δ < 2%

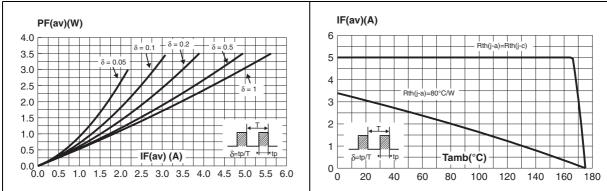
To evaluate the conduction losses use the following equation: P = 0.51 x $I_{F(AV)}$ + 0.02 $I_{F}{}^{2}{}_{(RMS)}$



5

Figure 1. Average forward power dissipation Figure 2. versus average forward current





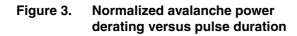


Figure 4. Normalized avalanche power derating versus junction temperature

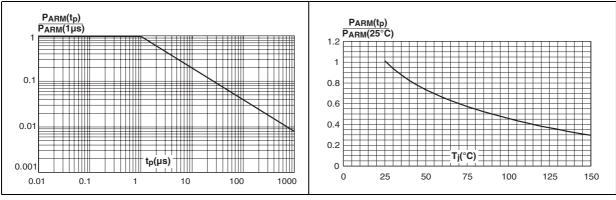
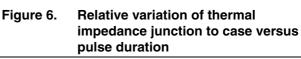
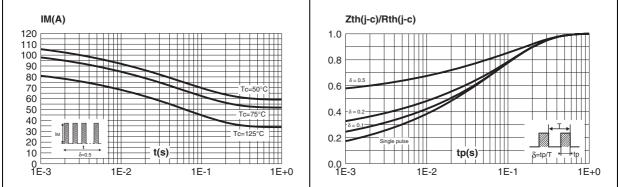


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values)

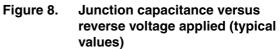




F=1MHz Tj=25°C

100

Figure 7. Reverse leakage current versus reverse voltage applied



C(pF)

1000

100

10 L

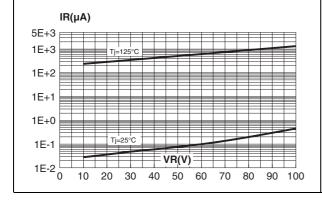
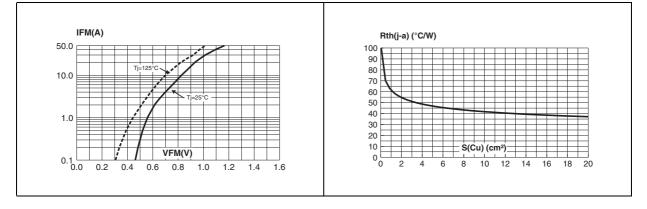




Figure 10. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: 35 µm)

VR(V)

10



2 Package information

- Cooling method: by conduction (C)
- Epoxy meets UL94, V0



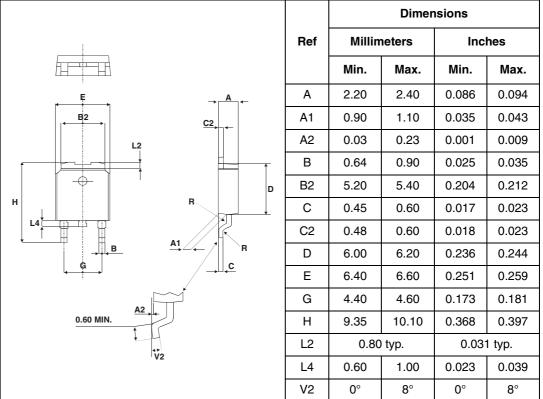
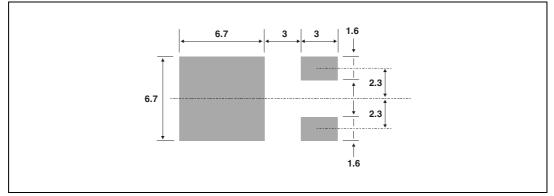


Figure 12. Footprint dimensions (in millimeters)



		Dimensions						
		Ref.	Mi	illimete	rs		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
	,	Α	2.20		2.40	0.086		0.094
		A1	0.90		1.10	0.035		0.043
		A3	0.70		1.30	0.027		0.051
		В	0.64		0.90	0.025		0.035
E	<u>C2</u>	B2	5.20		5.40	0.204		0.212
		B3			0.95			0.037
		B5		0.30			0.035	
		С	0.45		0.60	0.017		0.023
		C2	0.48		0.60	0.019		0.023
	A1	D	6		6.20	0.236		0.244
v 1		Е	6.40		6.60	0.252		0.260
eB5		е		2.28			0.090	
e → B5 G →		G	4.40		4.60	0.173		0.181
		Н		16.10			0.634	
		L	9		9.40	0.354		0.370
		L1	0.8		1.20	0.031		0.047
		L2		0.80	1		0.031	0.039
		V1		10°			10°	

Table 4.IPAK Dimensions

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.



3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS5H100B	S5H100	DPAK	0.30 g	75	Tube
STPS5H100B-TR	S5H100	DIAN	0.30 g	2500	Tape and reel
STPS5H100H	S5H100H	IPAK	0.40 g	75	Tube

4 Revision history

Date	Revision	Description of changes	
Jul-2003	6B	Last issue.	
03-Nov-2005	7	DPAK footprint dimensions updated.	
15-Feb-2006	8	ECOPACK statement added.	
05-Mar-2007	9	IPAK package added.	



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

